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STP2NK90Z - STD2NK90Z STD2NK90Z-1

N-channel 900V - 5Ω - 2.1A - TO-220 /DPAK/IPAK
Zener-Protected SuperMESH™ MOSFET

General features

Type	V _{DSS} (@T _{Jmax})	R _{DS(on)}	I _D	P _W
STD2NK90Z	900V	<6.5Ω	2.1A	70W
STD2NK90Z-1	900V	<6.5Ω	2.1A	70W
STP2NK90Z	900V	<6.5Ω	2.1A	70W

- Extremely high dv/dt capability
- Improved esd capability
- 100% avalanche rated
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeatability

Description

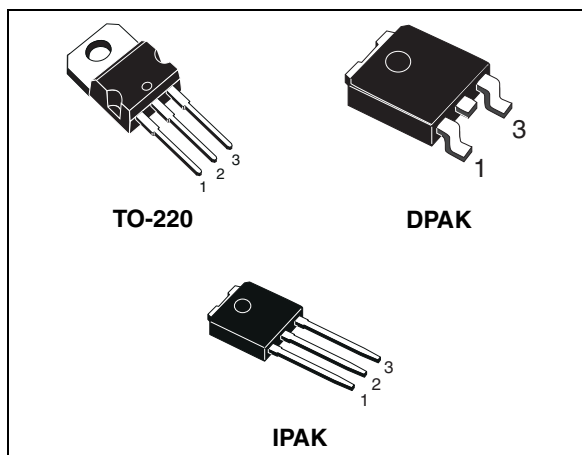
The SuperMESH™ series is obtained through an extreme optimization of ST's well established stripbased PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

Applications

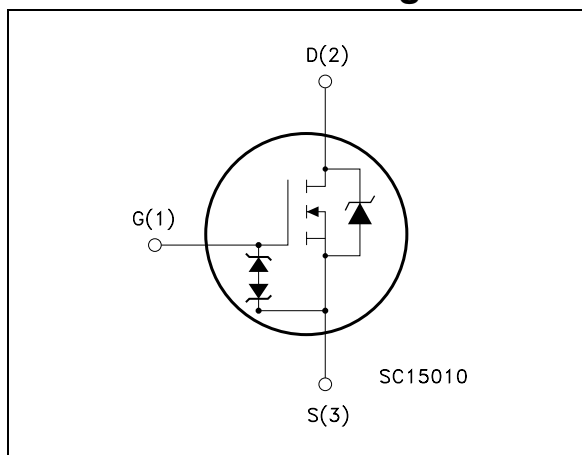
- Switching application

Order codes

Part number	Marking	Package	Packaging
STD2NK90ZT4	D2NK90Z	DPAK	Tape & reel
STD2NK90Z-1	D2NK90Z	IPAK	Tube
STP2NK90Z	P2NK90Z	TO-220	Tube



Internal schematic diagram



Contents

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		STP2NK90Z	STD2NK90Z STD2NK90Z-1	
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	900		V
V_{DGR}	Drain-gate voltage ($R_{GS} = 20\text{ k}\Omega$)	900		V
V_{GS}	Gate- source Voltage	± 30		V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	2.1		A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	1.3		A
$I_{DM}^{(1)}$	Drain current (pulsed)	8.4		A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	70		W
	Derating factor	0.56		W/ $^\circ\text{C}$
$V_{ESD(G-S)}$	Gate source ESD(HBM-C=100pF, R=1.5K Ω)	2000		V
$dv/dt^{(2)}$	Peak diode recovery voltage slope	4.5		V/ns
T_j	Operating junction temperature	-55 to 150		$^\circ\text{C}$
T_{stg}	Storage temperature	-55 to 150		$^\circ\text{C}$

1. Pulse width limited by safe operating area

2. $I_{SD} \leq 2.1\text{ A}$, $di/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
Rthj-case	Thermal resistance junction-case max	1.78	$^\circ\text{C}/\text{W}$
Rthj-amb	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	2.1	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	150	mJ

Table 4. Gate-source zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-source breakdown voltage	$I_{GS}=\pm 1\text{ mA}$ (open drain)	30			V

1.1 Protection features of gate-to-source zener diodes

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown Voltage	$I_D = 1 \text{ mA}, V_{GS} = 0$	900			V
I_{DSS}	Zero gate voltage	$V_{DS} = \text{Max Rating}$			1	μA
	Drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}, T_C = 125^{\circ}C$			50	μA
I_{GSS}	Gate-body Leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20 \text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 50 \mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}, I_D = 1.05 \text{ A}$		5	6.5	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15 \text{ V}, I_D = 1.05 \text{ A}$		2.3		S
C_{iss} C_{oss} C_{rss}	Input capacitance	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz},$ $V_{GS} = 0$		485		pF
	Output capacitance			50		pF
	Reverse transfer capacitance			10		pF
$C_{oss \text{ eq}}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 0 \text{ to } 720 \text{ V}$		24		pF
Q_g Q_{gs} Q_{gd}	Total gate charge	$V_{DD} = 720 \text{ V}, I_D = 2 \text{ A},$ $V_{GS} = 10 \text{ V}$ (see Figure 22)		19.5	27	nC
	Gate-source charge			3.4		nC
	Gate-drain charge			10.8		nC

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2. $C_{oss \text{ eq}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 450 \text{ V}, I_D = 1 \text{ A},$ $R_G = 4.7 \Omega, V_{GS} = 10 \text{ V}$ (see Figure 19)		21		ns
t_r	Rise time			11		ns
$t_{d(off)}$	Turn-off delay time			43		ns
t_f	Fall time			40		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				2.1	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				8.4	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 2.1 \text{ A}, V_{GS} = 0$			1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 2 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 50\text{V}$ (see Figure 20)		415		ns
Q_{rr}	Reverse recovery charge			1.5		μC
I_{RRM}	Reverse recovery current			7.2		A
t_{rr}	Reverse recovery time	$I_{SD} = 2 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 50\text{V}, T_j = 150^\circ\text{C}$ (see Figure 20)		515		ns
Q_{rr}	Reverse recovery charge			1.9		μC
I_{RRM}	Reverse recovery current			7.5		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area for TO-220/ DPAK/ D²PAK

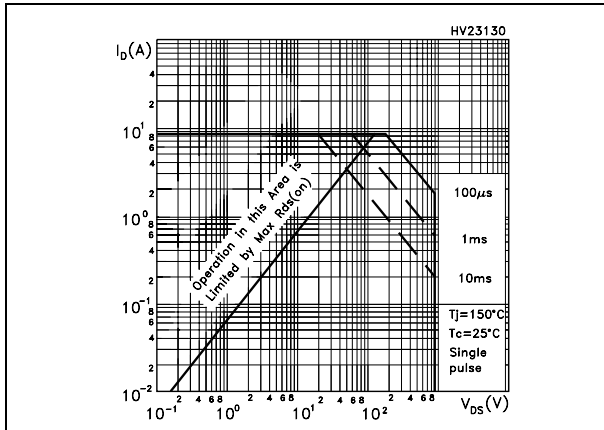


Figure 2. Thermal impedance for TO-220/ DPAK/ D²PAK

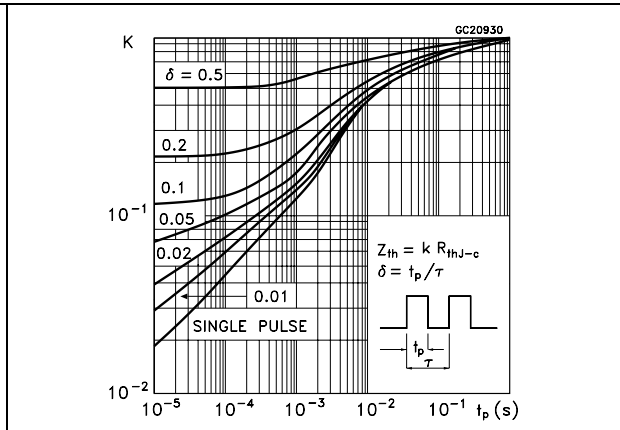


Figure 3. Safe operating area for TO-220FP

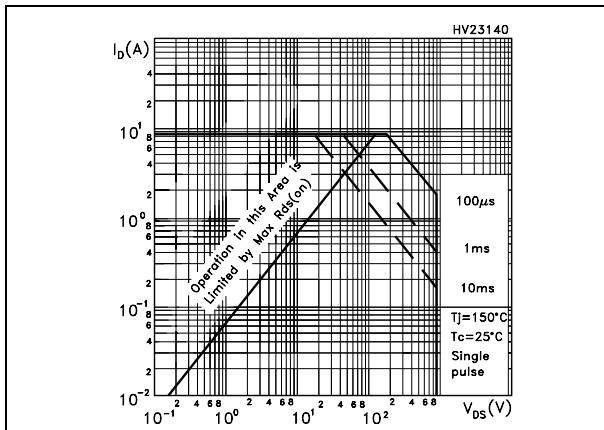


Figure 4. Thermal impedance for TO-220FP

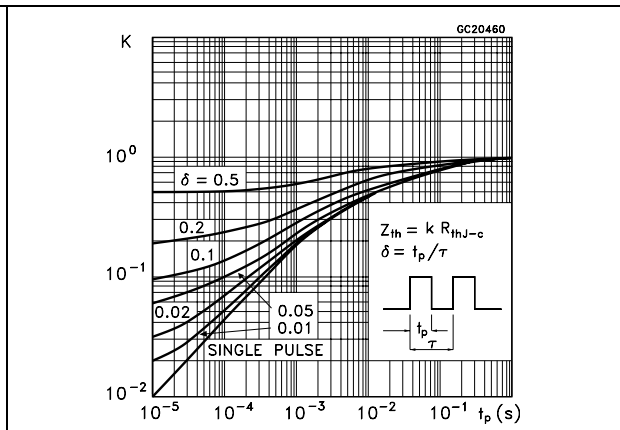


Figure 5. Output characteristics

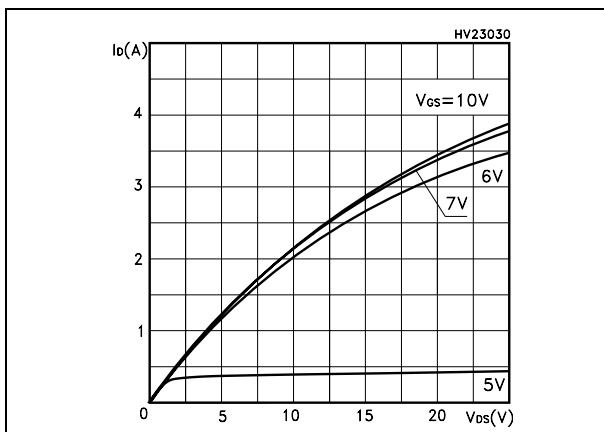


Figure 6. Transfer characteristics

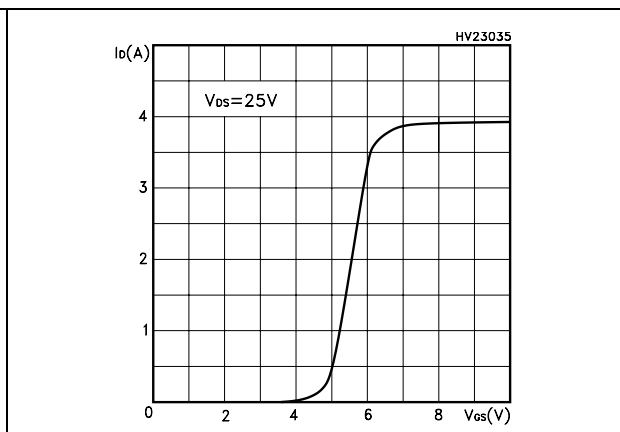


Figure 7. Transconductance

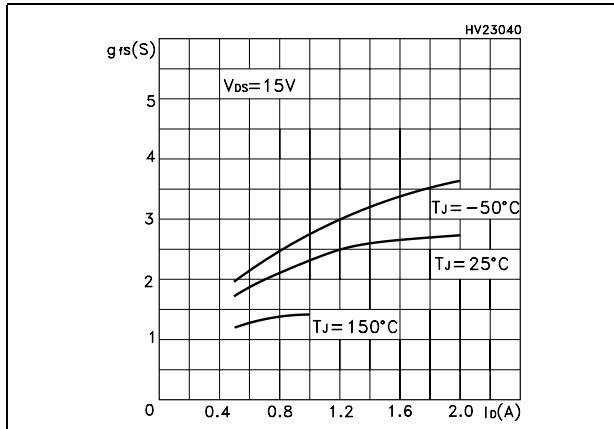


Figure 8. Static drain-source on resistance

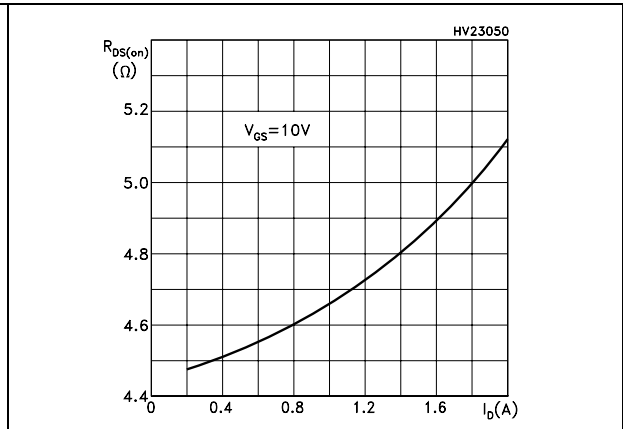


Figure 9. Gate charge vs gate-source voltage

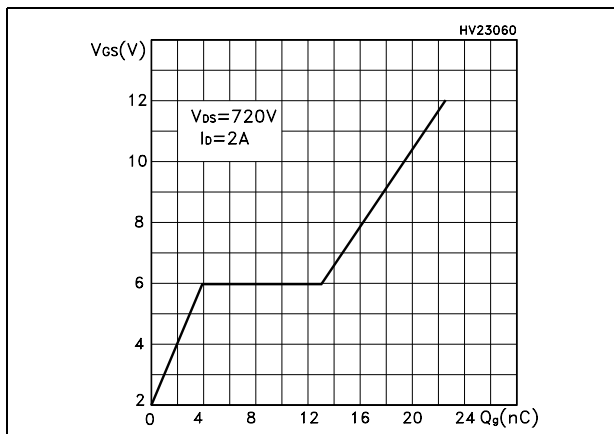


Figure 10. Capacitance variations

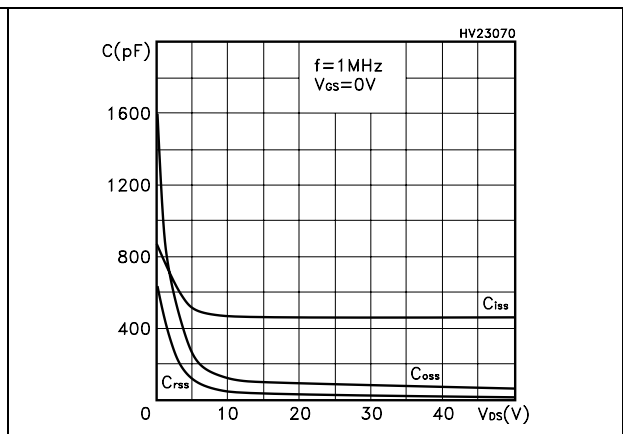


Figure 11. Normalized gate threshold voltage vs temperature

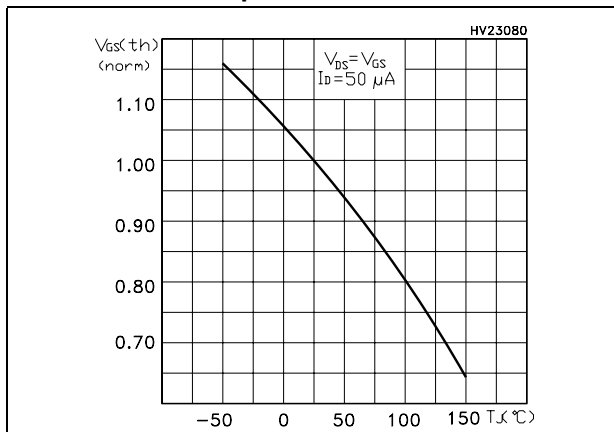


Figure 12. Normalized on resistance vs temperature

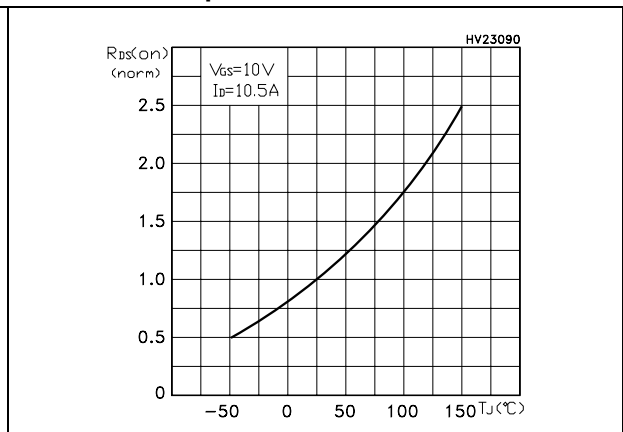


Figure 13. Source-drain diode forward characteristics

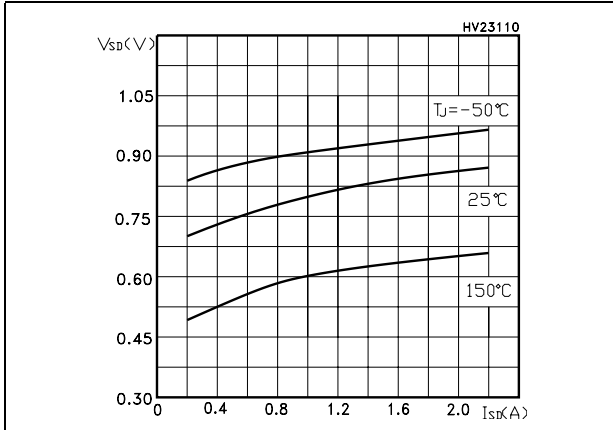


Figure 14. Normalized B_{VDSS} vs temperature

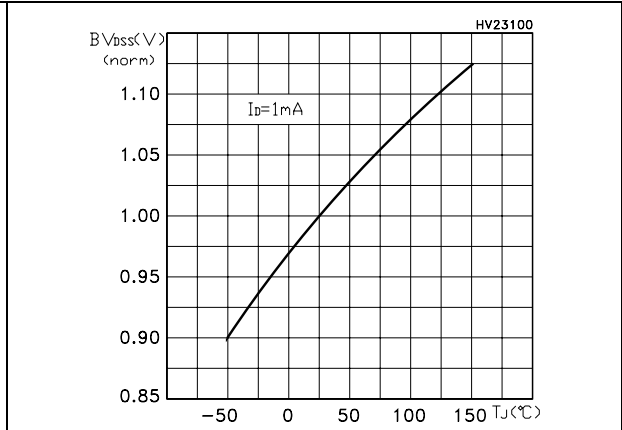
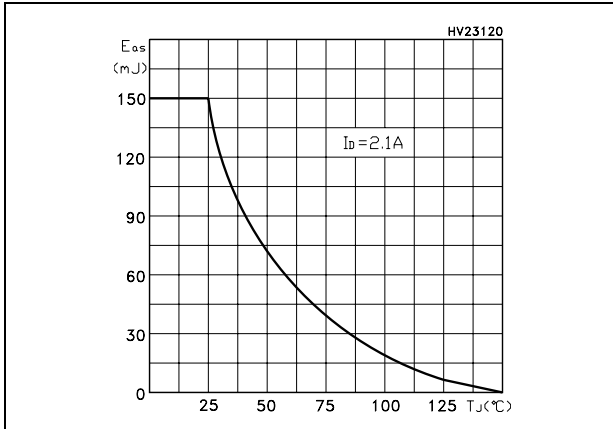


Figure 15. Maximum avalanche energy vs temperature



3 Test circuit

Figure 16. Switching times test circuit for resistive load

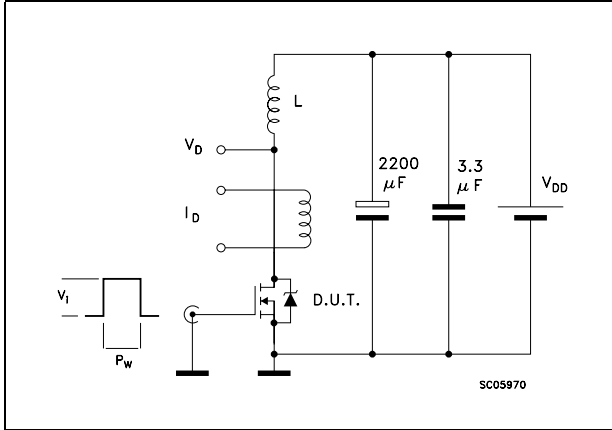


Figure 17. Gate charge test circuit

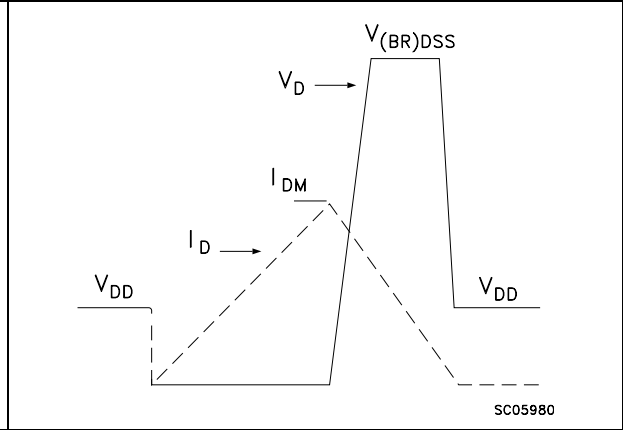


Figure 18. Test circuit for inductive load switching and diode recovery times

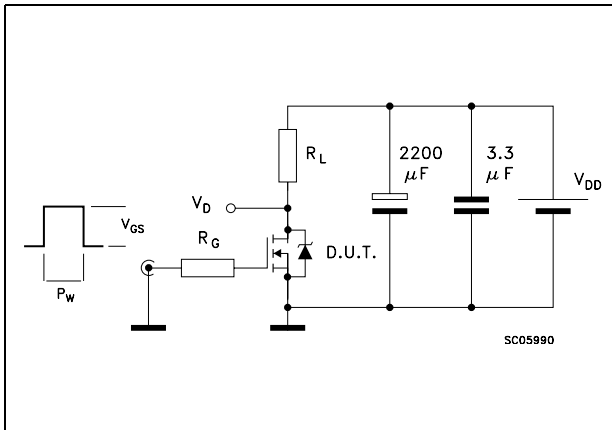


Figure 19. Unclamped Inductive load test circuit

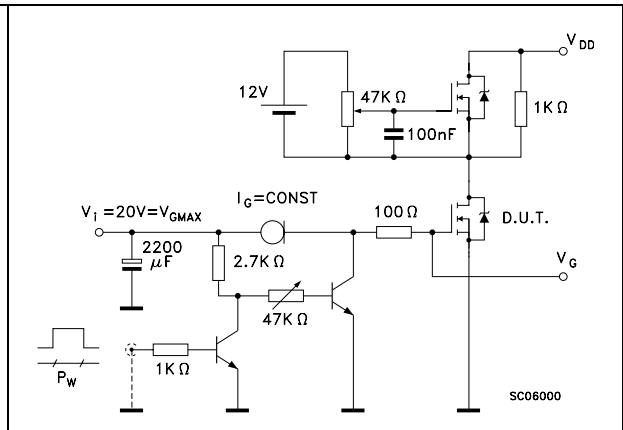
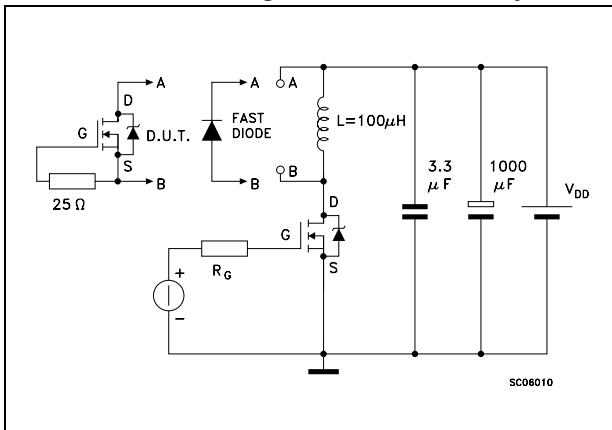


Figure 20. Test circuit for inductive load switching and diode recovery times

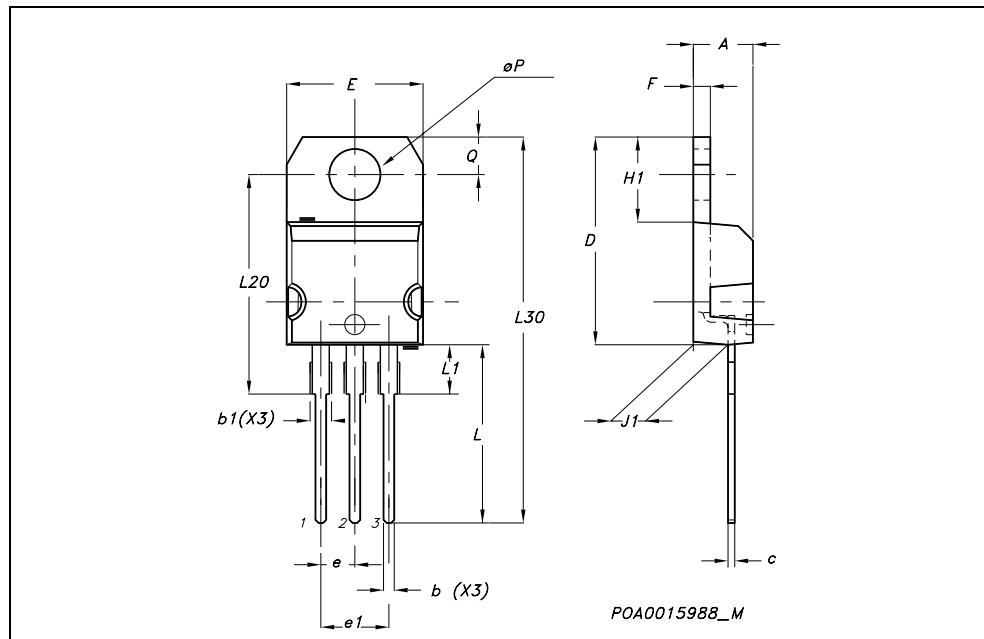


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

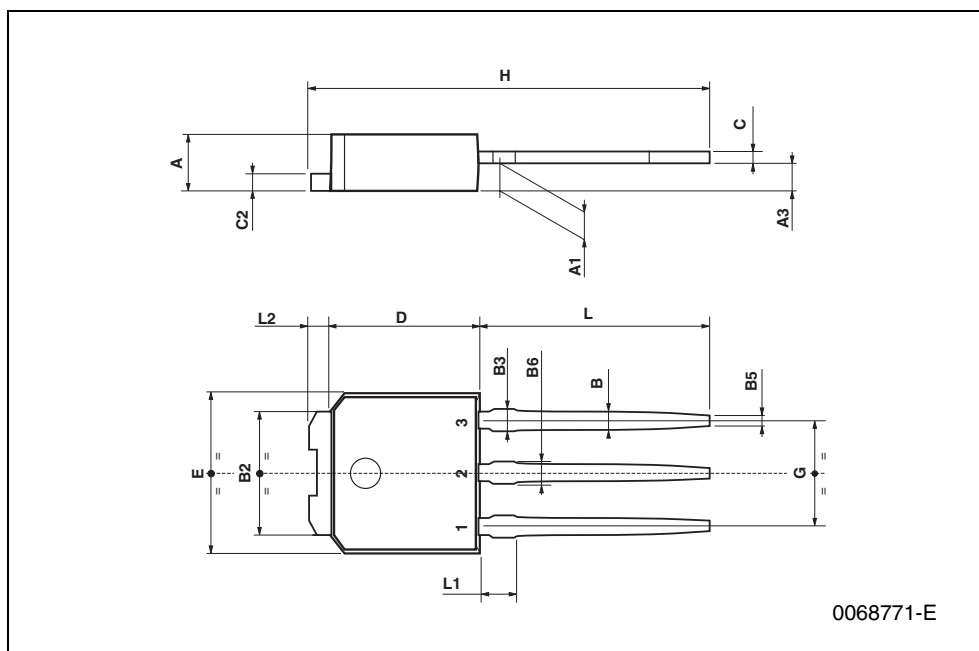
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



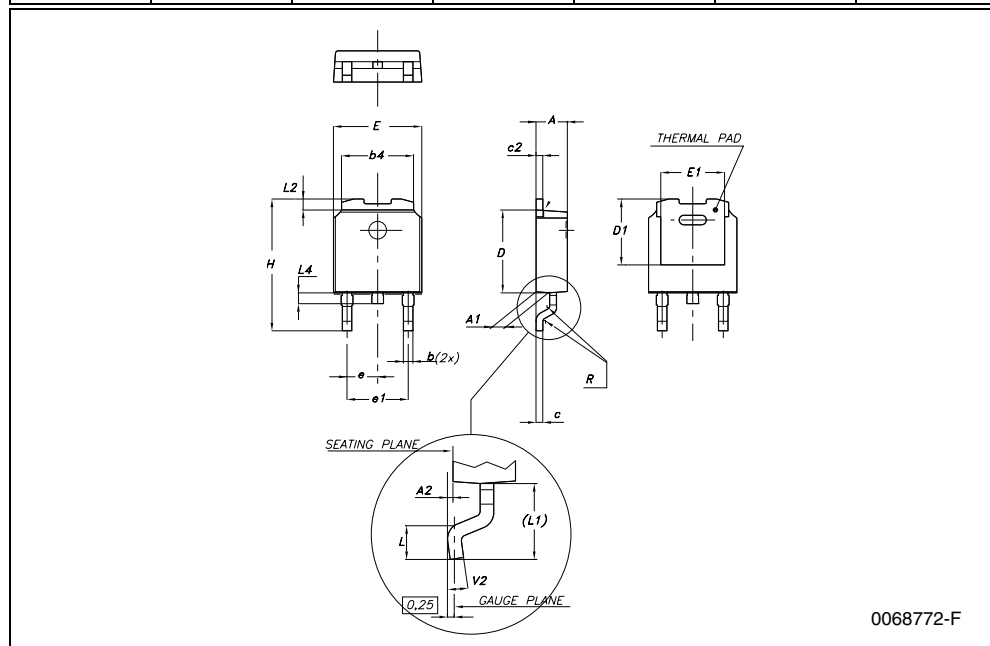
TO-251 (IPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



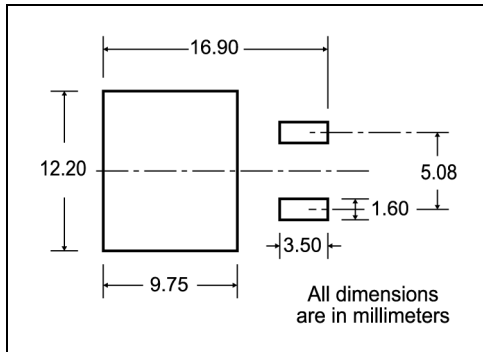
DPAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
E	6.4		6.6	0.252		0.260
E1		4.7			0.185	
e		2.28			0.090	
e1	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°



5 Packing mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

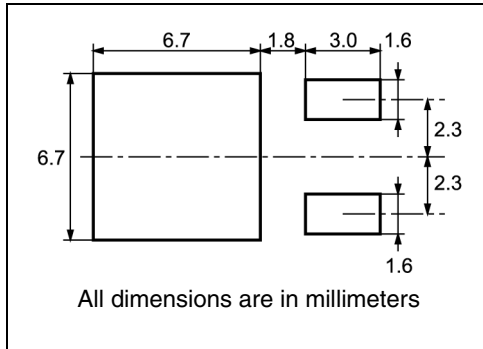
REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

* on sales type

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT

40 mm min. Access hole at slot location

Full radius

Tape slot in core for tape start 2.5mm min. width

G measured at hub

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
2500	2500

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

10 pitches cumulative tolerance on tape +/- 0.2 mm

Center line of cavity

For machine ref. only including draft and radii concentric around B0

FEED DIRECTION

Bending radius R min.

6 Revision history

Table 9. Revision history

Date	Revision	Changes
06-Oct-2004	1	First version
08-Sep-2005	2	Complete version
05-Mar-2006	3	Inserted Ecopack indication
27-Jul-2006	4	New template, no content change

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